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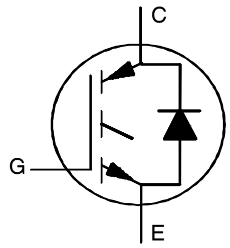
IRGB4045DPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE



n-channel

V_{CES} = 600V

I_C = 6.0A, T_C = 100°C

t_{sc} > 5µs, T_{jmax} = 175°C

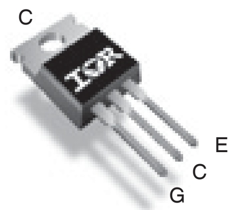
$V_{CE(on)}$ typ. = 1.7V

Features

- Low $V_{CE\ (on)}$ Trench IGBT Technology
- Low Switching Losses
- Maximum Junction temperature 175 °C
- 5µs SCSOA
- Square RBSOA
- 100% of the parts tested for I_{LM} ①
- Positive $V_{CE\ (on)}$ Temperature Coefficient.
- Ultra Fast Soft Recovery Co-pak Diode
- Tighter Distribution of Parameters
- Lead-Free Package

Benefits

- High Efficiency in a Wide Range of Applications
- Suitable for a Wide Range of Switching Frequencies due to Low $V_{CE\ (ON)}$ and Low Switching Losses
- Rugged Transient Performance for Increased Reliability
- Excellent Current Sharing in Parallel Operation
- Low EMI



TO-220AB

G	C	E
Gate	Collector	Emitter

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Breakdown Voltage	600	V
I_C @ T_C = 25°C	Continuous Collector Current	12	A
I_C @ T_C = 100°C	Continuous Collector Current	6.0	
I_{CM}	Pulsed Collector Current, V_{GE} = 15V	18	
I_{LM}	Clamped Inductive Load Current, V_{GE} = 20V ①	24	
I_F@T_C=25°C	Diode Continuous Forward Current	8.0	
I_F@T_C=100°C	Diode Continuous Forward Current	4.0	
I_{FM}	Diode Maximum Forward Current ②	24	
V_{GE}	Continuous Gate-to-Emitter Voltage	± 20	V
	Transient Gate-to-Emitter Voltage	± 30	
P_D @ T_C =25°	Maximum Power Dissipation	77	W
P_D @ T_C =100°	Maximum Power Dissipation	39	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm) from case)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT ③	—	—	1.94	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode ③	—	—	6.30	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.5	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount ③	—	—	62	

01/28/2010

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V_{GE} = 0V, I_c =100 µA ④	CT6
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.36	—	V/°C	V_{GE} = 0V, I_c = 250µA (25 -175 °C) ④	
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.7	2.0	V	I_C = 6.0A, V_{GE} = 15V, T_J = 25°C	5,6,7,9, 10 ,11
		—	2.07	—		I_C = 6.0A, V_{GE} = 15V, T_J = 150°C	
		—	2.14	—		I_C = 6.0A, V_{GE} = 15V, T_J = 175°C	
$V_{GE(th)}$	Gate Threshold Voltage	4.0	—	6.5	V	V_{CE} = V_{GE}, I_C = 150µA	9,10,11,12
$\Delta V_{GE(th)}/\Delta TJ$	Threshold Voltage temp. coefficient	—	-13	—	mV/°C	V_{CE} = V_{GE}, I_C = 250µA (25 -175 °C)	
gfe	Forward Transconductance	—	5.8	—	S	V_{CE} = 25V, I_C = 6.0A, PW =80µs	
I_{CES}	Collector-to-Emitter Leakage Current	—	—	25	µA	V_{GE} = 0V,V_{CE} = 600V	8
		—	—	250		V_{GE} = 0V, V_{CE} = 600V, T_J =175°C	
V_{FM}	Diode Forward Voltage Drop	—	1.60	2.30	V	I_F = 6.0A	
		—	1.30	—		I_F = 6.0A, T_J = 175°C	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ± 20 V	

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig
Q_g	Total Gate Charge (turn-on)	—	13	19.5	nC	I_C = 6.0A	24
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	3.1	4.65		V_{CC} = 400V	CT1
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	6.4	9.6		V_{GE} = 15V	
E_{on}	Turn-On Switching Loss	—	56	86	µJ	I_C = 6.0A, V_{CC} = 400V, V_{GE} = 15V	CT4
E_{off}	Turn-Off Switching Loss	—	122	143		R_G = 47Ω, L=1mH, L_S= 150nH, T_J = 25°C	
E_{total}	Total Switching Loss	—	178	229		Energy losses include tail and diode reverse recovery	
$t_{d(on)}$	Turn-On delay time	—	27	35	ns	I_C = 6.0A, V_{CC} = 400V	CT4
t_r	Rise time	—	11	15		R_G = 47Ω, L=1mH, L_S= 150nH	
$t_{d(off)}$	Turn-Off delay time	—	75	93		T_J = 25°C	
t_f	Fall time	—	17	22			
E_{on}	Turn-On Switching Loss	—	140	—	µJ	I_C = 6.0A, V_{CC} = 400V, V_{GE} = 15V	13,15
E_{off}	Turn-Off Switching Loss	—	189	—		R_G = 47Ω, L=1mH, L_S= 150nH, T_J = 175°C	CT4
E_{total}	Total Switching Loss	—	329	—		Energy losses include tail and diode reverse recovery	WF1,WF2
$t_{d(on)}$	Turn-On delay time	—	26	—	ns	I_C = 6.0A, V_{CC} = 400V	14,16
t_r	Rise time	—	12	—		R_G = 47Ω, L=1mH, L_S= 150nH	CT4
$t_{d(off)}$	Turn-Off delay time	—	95	—		T_J = 175°C	WF1,WF2
t_f	Fall time	—	32	—			
C_{ies}	Input Capacitance	—	350	—	pF	V_{GE} = 0V	23
C_{oes}	Output Capacitance	—	29	—		V_{CC} = 30V	
C_{res}	Reverse Transfer Capacitance	—	10	—		f = 1Mhz	
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T_J = 175°C, I_C = 24A V_{CC} = 500V, Vp =600V R_G = 100Ω, V_{GE} = +20V to 0V	4 CT2
SCSOA	Short Circuit Safe Operating Area	5	—	—	µs	V_{CC} = 400V, Vp =600V R_G = 100Ω, V_{GE} = +15V to 0V	22, CT3 WF4
Erec	Reverse recovery energy of the diode	—	178	—	µJ	T_J = 175°C	17,18,19
trr	Diode Reverse recovery time	—	74	—	ns	V_{CC} = 400V, I_F = 6.0A	20,21
Irr	Peak Reverse Recovery Current	—	12	—	A	V_{GE} = 15V, Rg = 47Ω, L=1mH, L_S=150nH	WF3

Notes:

① V_{CC} = 80% (V_{CES}), V_{GE} = 15V, L = 1.0mH, R_G = 47Ω.
② Pulse width limited by max. junction temperature.
③ R_θ is measured at T_J approximately 90°C.
④ Refer to AN-1086 for guidelines for measuring $V_{(BR)CES}$ safely.

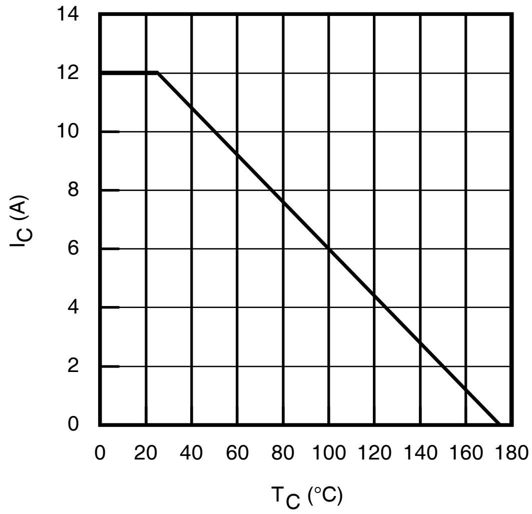


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

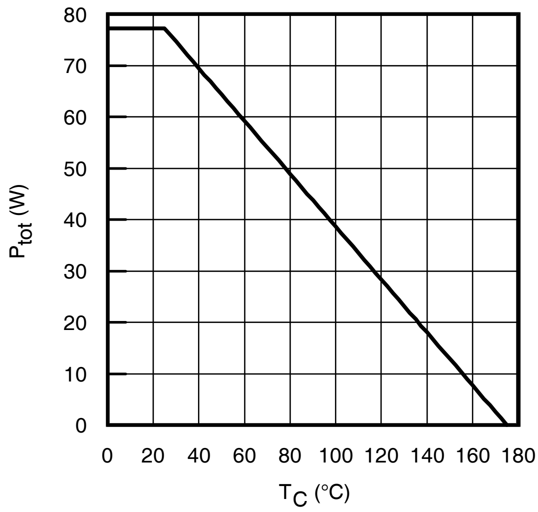


Fig. 2 - Power Dissipation vs. Case Temperature

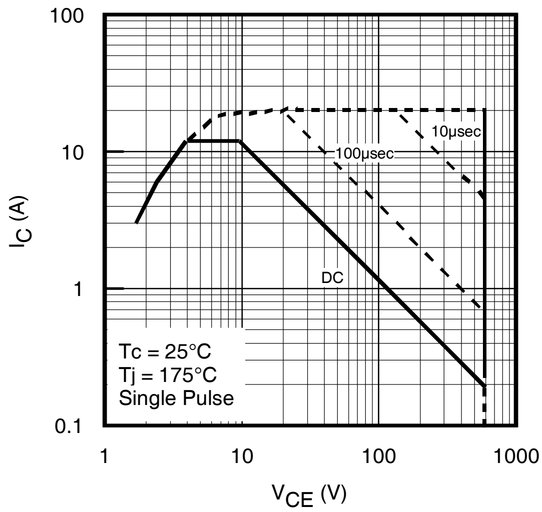


Fig. 3 - Forward SOA, T_C = 25°C, $T_J \leq$ 175°C, V_{GE} = 15V

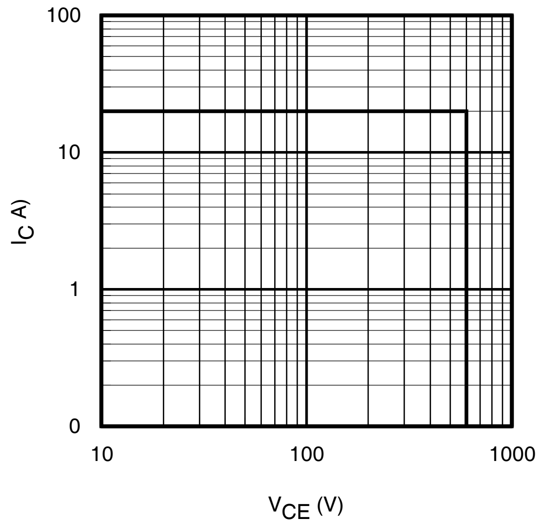


Fig. 4 - Reverse Bias SOA T_J = 175°C, V_{GE} = 20V

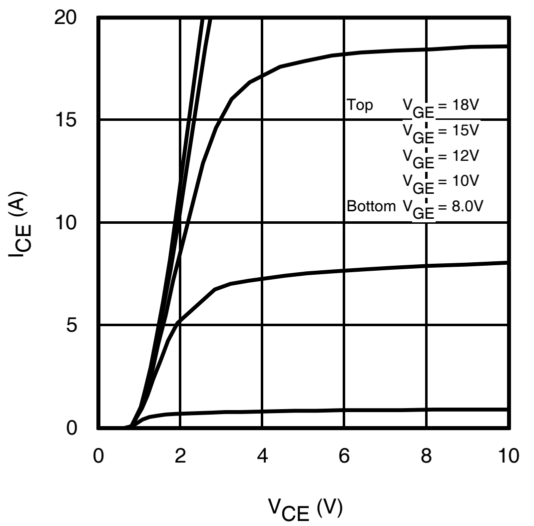


Fig. 5 - Typ. IGBT Output Characteristics T_J = -40°C; tp = 80µs

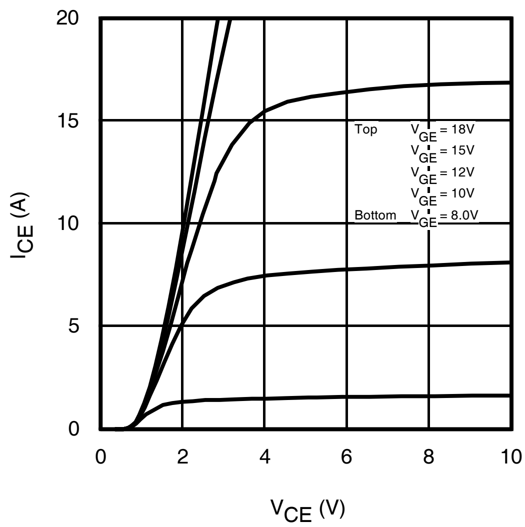


Fig. 6 - Typ. IGBT Output Characteristics T_J = 25°C; tp = 80µs

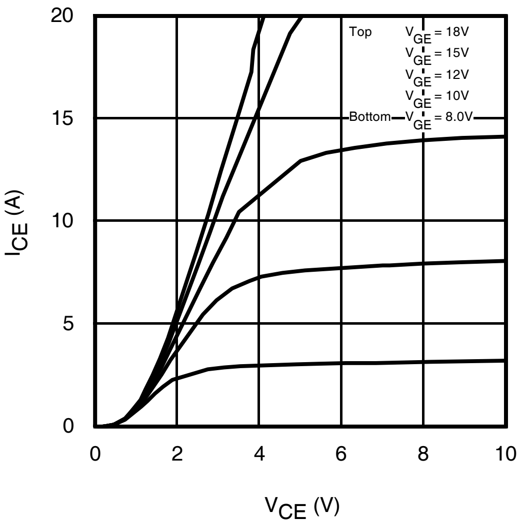


Fig. 7 - Typ. IGBT Output Characteristics
T_J = 175°C; tp = 80μs

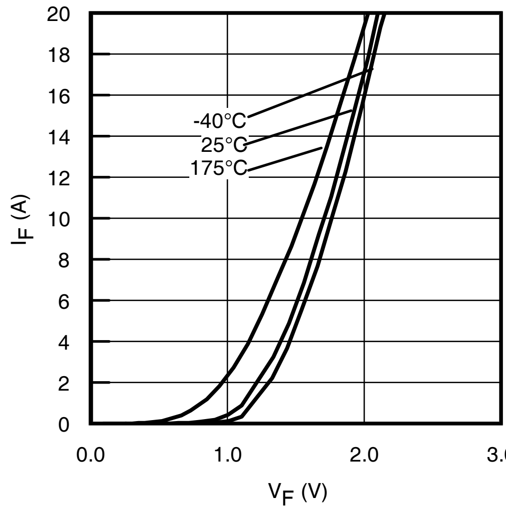


Fig. 8 - Typ. Diode Forward Characteristics
tp = 80μs

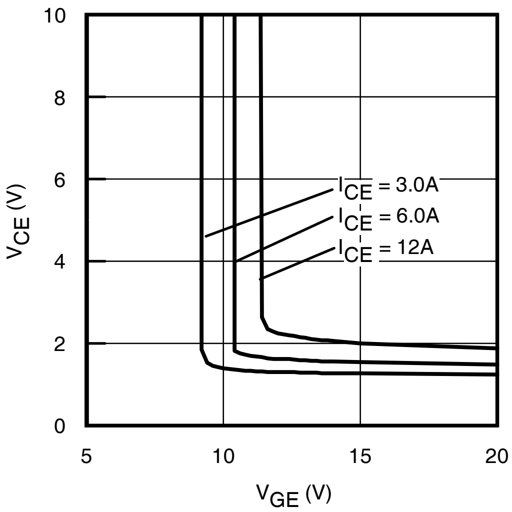


Fig. 9 - Typical V_{CE} vs. V_{GE}
T_J = -40°C

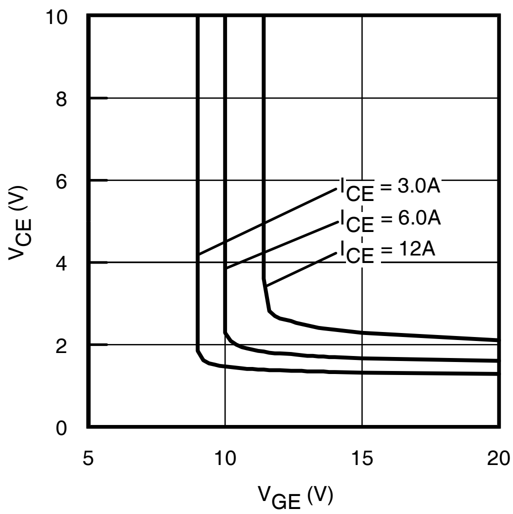


Fig. 10 - Typical V_{CE} vs. V_{GE}
T_J = 25°C

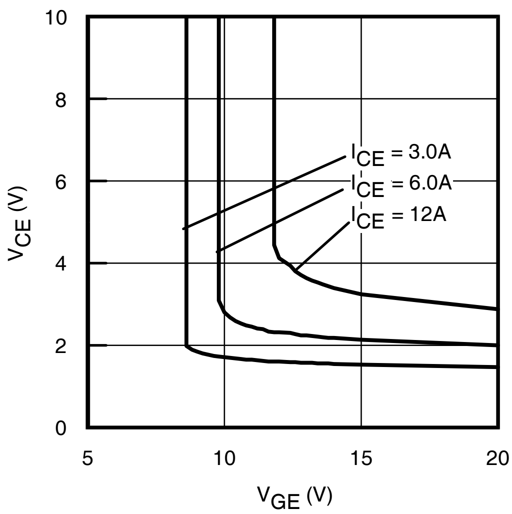


Fig. 11 - Typical V_{CE} vs. V_{GE}
T_J = 175°C

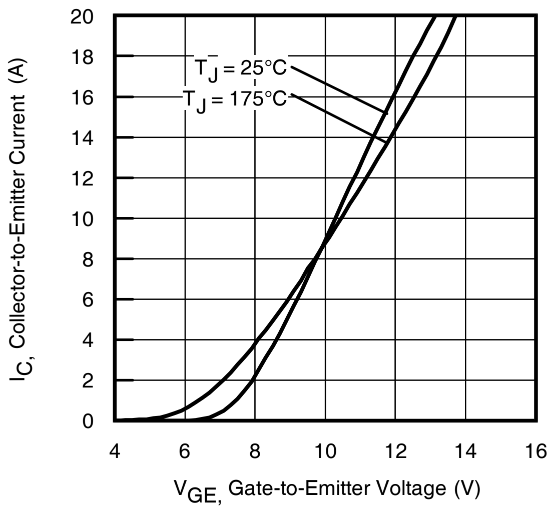


Fig. 12 - Typ. Transfer Characteristics
V_{CE} = 50V; tp = 10μs

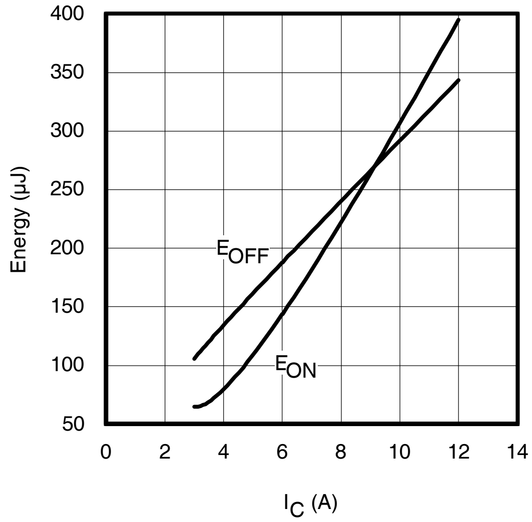


Fig. 13 - Typ. Energy Loss vs. I_C
T_J = 175°C; L = 1mH; V_{CE} = 400V, R_G = 47Ω; V_{GE} = 15V.

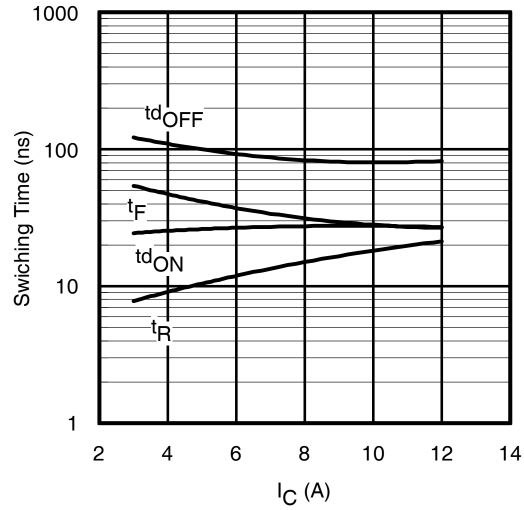


Fig. 14 - Typ. Switching Time vs. I_C
T_J = 175°C; L=1mH; V_{CE}= 400V
R_G= 47Ω; V_{GE}= 15V

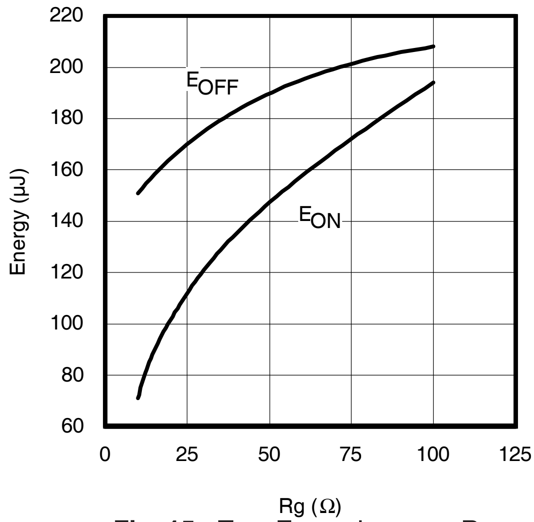


Fig. 15 - Typ. Energy Loss vs. R_G
T_J = 175°C; L = 1mH; V_{CE} = 400V, I_{CE} = 6.0A; V_{GE} = 15V

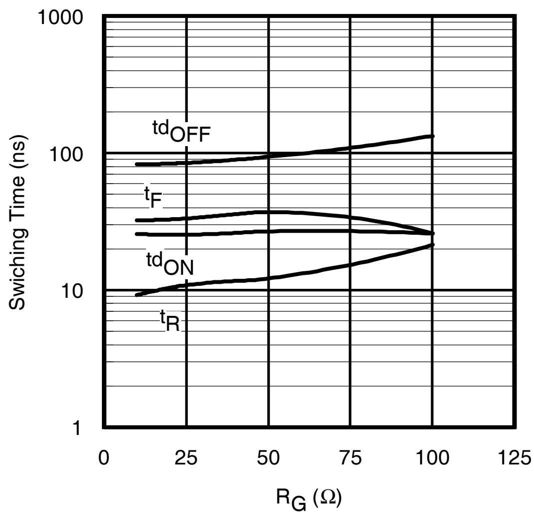


Fig. 16- Typ. Switching Time vs. R_G
T_J = 175°C; L=1mH; V_{CE}= 400V
I_{CE}= 6.0A; V_{GE}= 15V

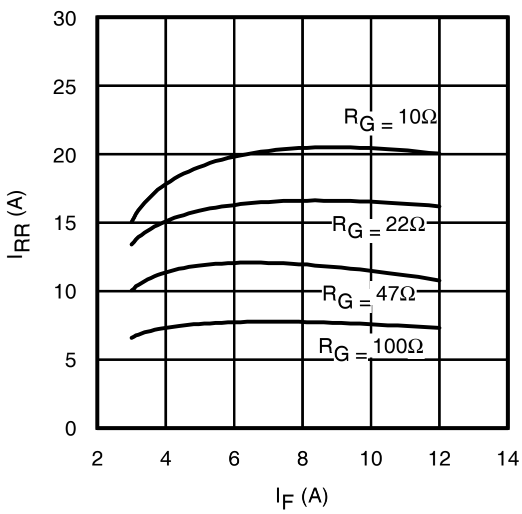


Fig. 17 - Typical Diode I_{RR} vs. I_F
T_J = 175°C

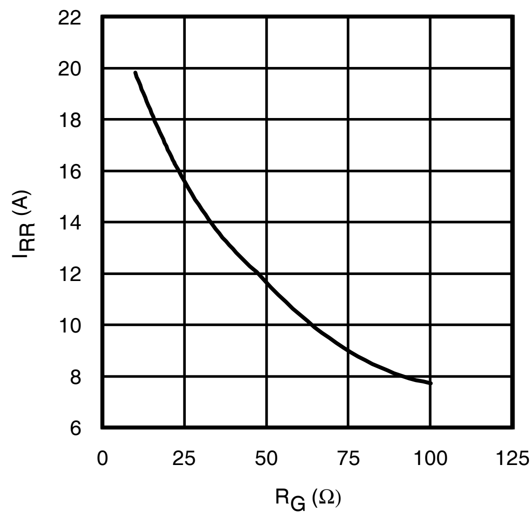


Fig. 18 - Typical Diode I_{RR} vs. R_G
T_J = 175°C; I_F = 6.0A

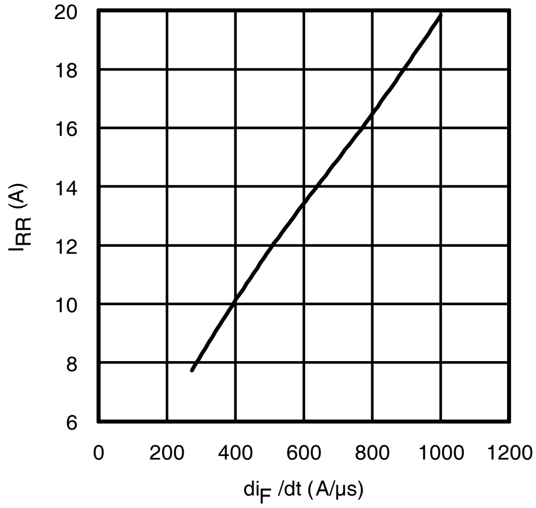


Fig. 19- Typical Diode I_{RR} vs. di_F/dt
V_{CC}= 400V; V_{GE}= 15V;
I_{CE}= 6.0A; T_J = 175°C

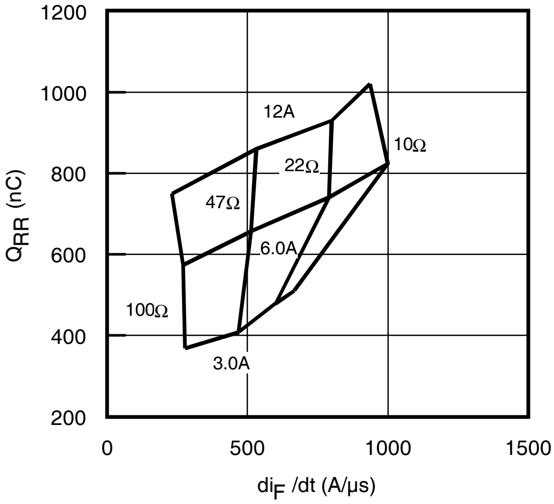


Fig. 20 - Typical Diode Q_{RR}
V_{CC}= 400V; V_{GE}= 15V; T_J = 175°C

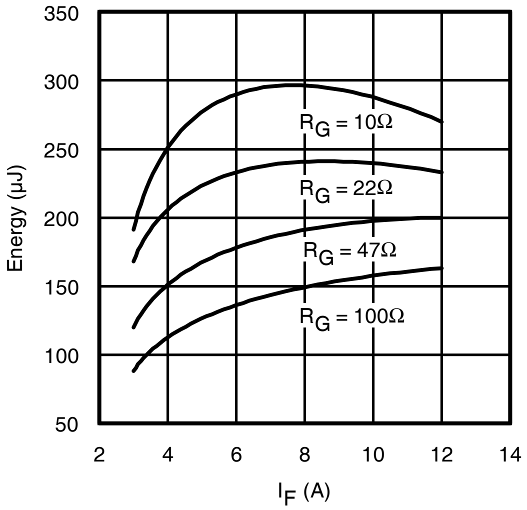


Fig. 21 - Typical Diode E_{RR} vs. I_F
T_J = 175°C

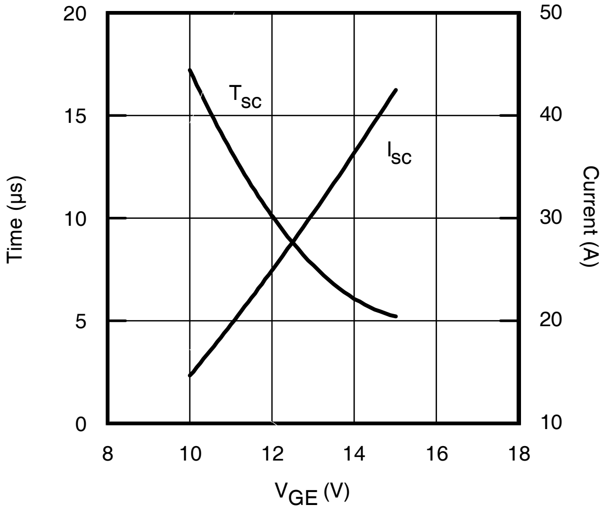


Fig. 22- Typ. V_{GE} vs. Short Circuit Time
V_{CC}=400V, T_C =25°C

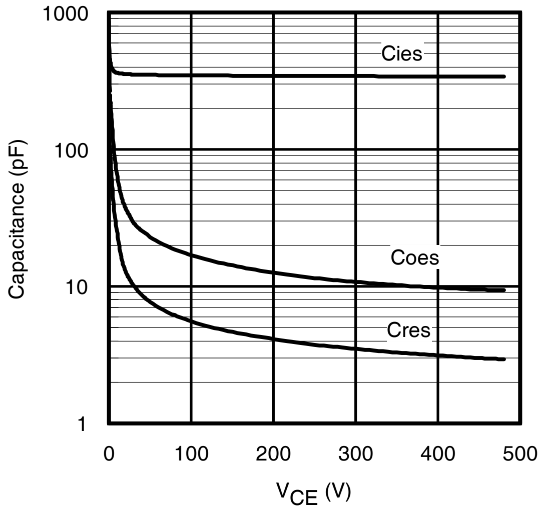


Fig. 23- Typ. Capacitance vs. V_{CE}
V_{GE}= 0V; f = 1MHz

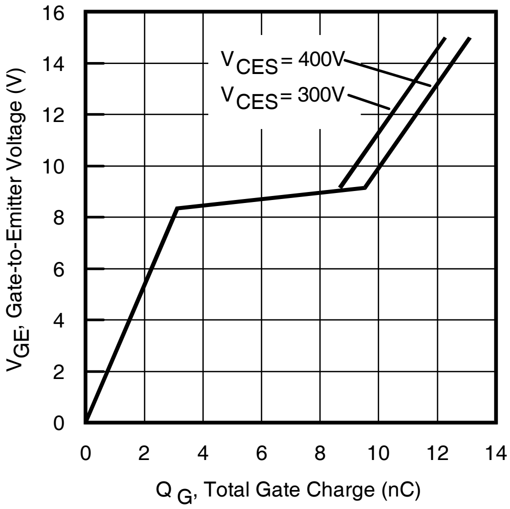


Fig. 24 - Typical Gate Charge vs. V_{GE}
I_{CE} = 6.0A, L=600µH

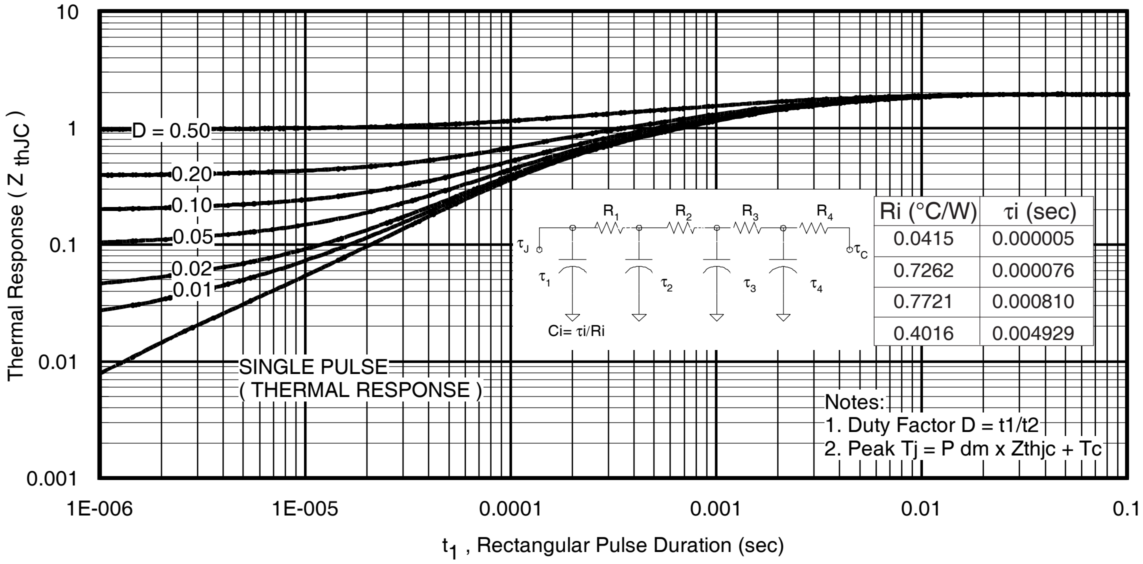


Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

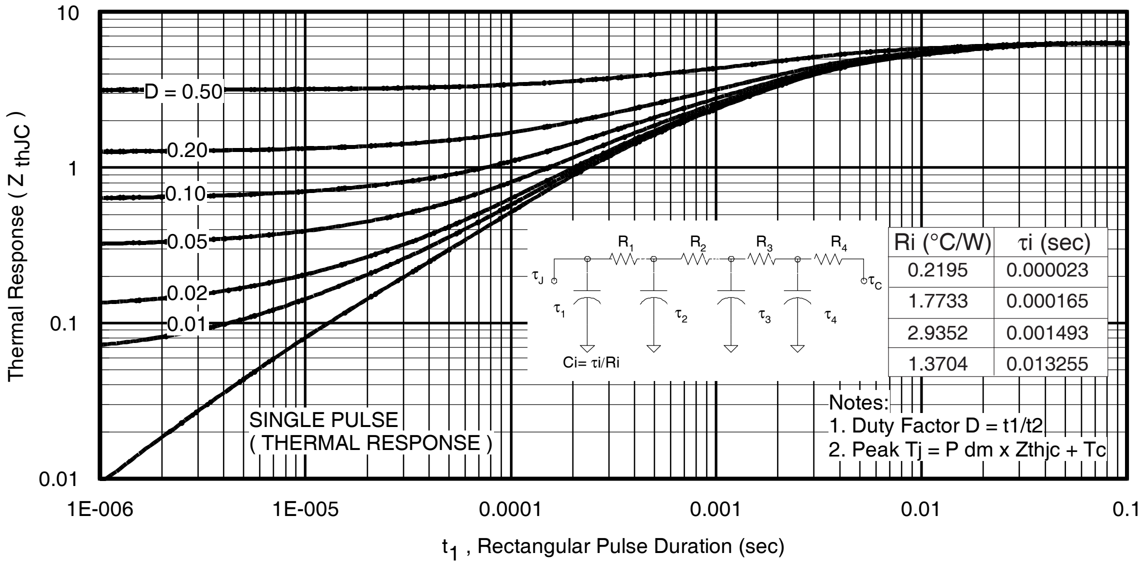


Fig. 26. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)

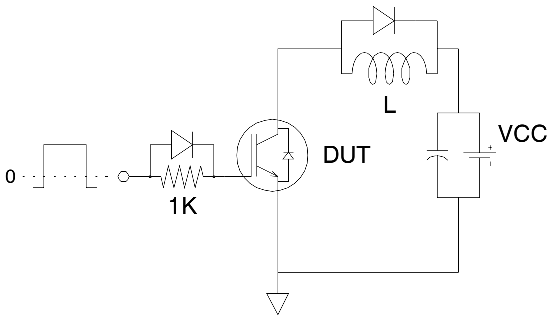


Fig.C.T.1 - Gate Charge Circuit (turn-off)

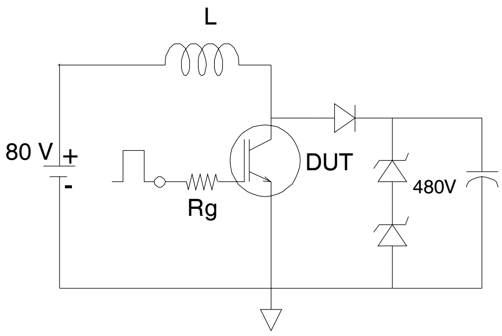


Fig.C.T.2 - RBSOA Circuit

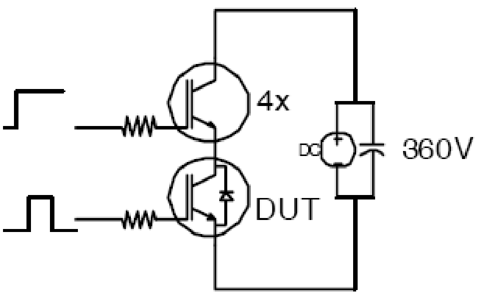


Fig.C.T.3 - S.C.SOA Circuit

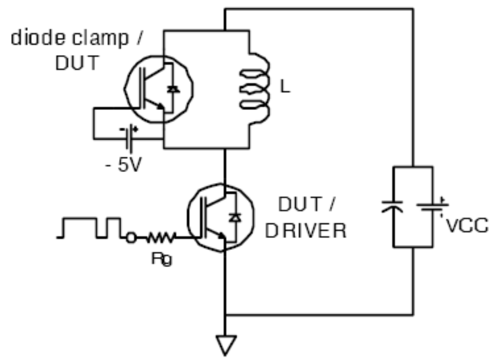


Fig.C.T.4 - Switching Loss Circuit

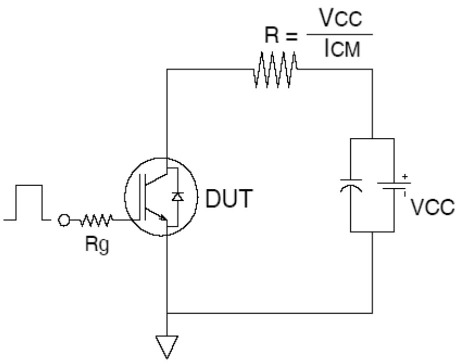


Fig.C.T.5 - Resistive Load Circuit

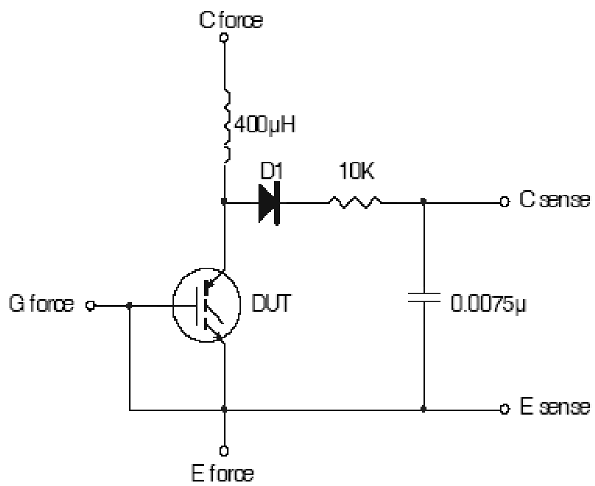


Fig.C.T.6 - Typical Filter Circuit for $V_{(BR)CES}$ Measurement

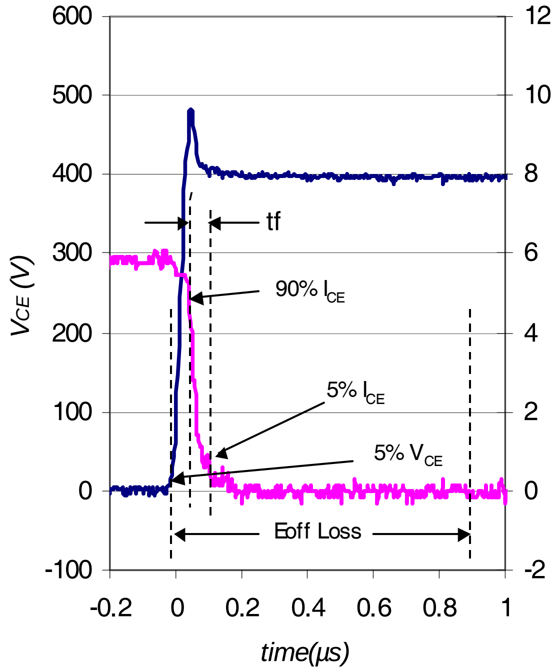


Fig. WF1 - Typ. Turn-off Loss Waveform
@ T_J = 175°C using Fig. CT.4

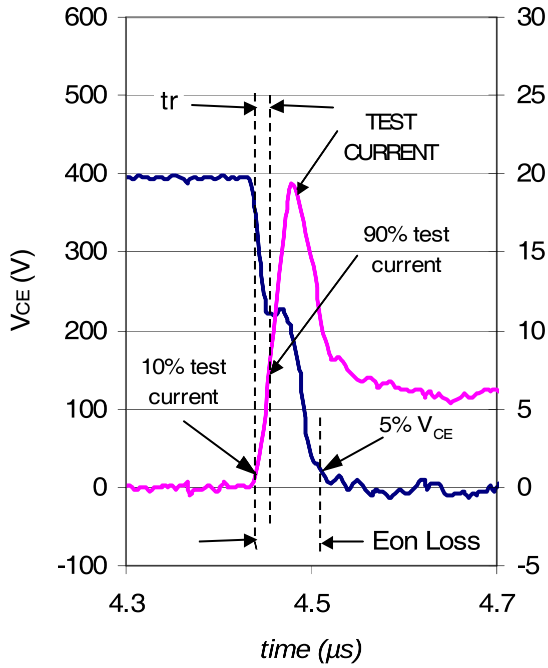
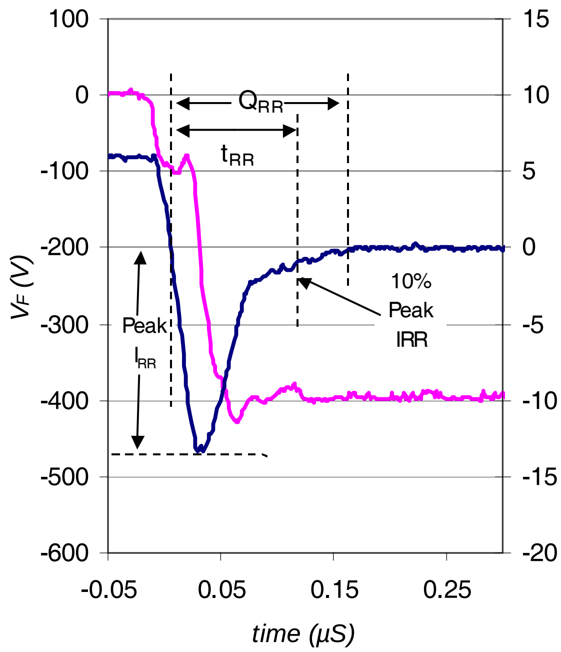
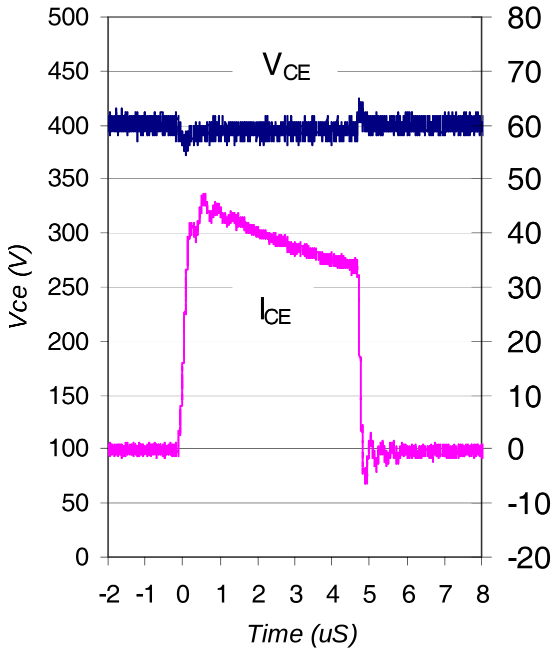


Fig. WF2 - Typ. Turn-on Loss Waveform
@ T_J = 175°C using Fig. CT.4

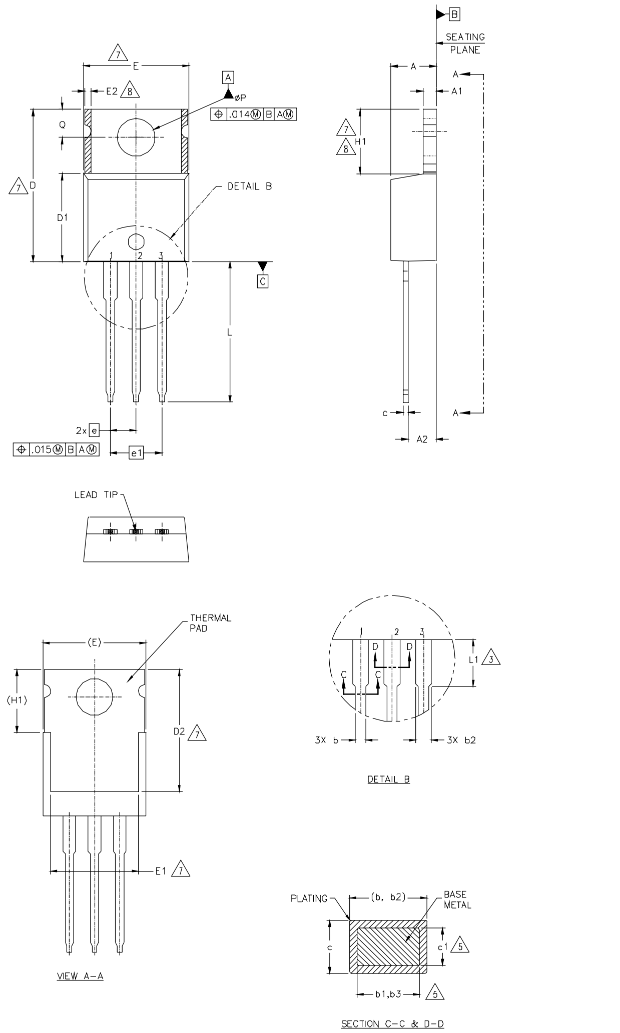


WF.3- Typ. Diode Recovery Waveform
@ T_J = 175°C using CT.4



WF.4- Typ. Short Circuit Waveform
@ T_J = 25°C using CT.3

TO-220AB Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

1.– DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M– 1994.
2.– DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
3.– LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
4.– DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5.– DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
6.– CONTROLLING DIMENSION : INCHES.
7.– THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
8.– DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
9.– OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	–	0.76	–	.030	8
e	2.54 BSC		.100 BSC		
e1	5.08 BSC		.200 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	–	6.35	–	.250	3
øP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

LEAD ASSIGNMENTS

HEXFET
1.– GATE
2.– DRAIN
3.– SOURCE

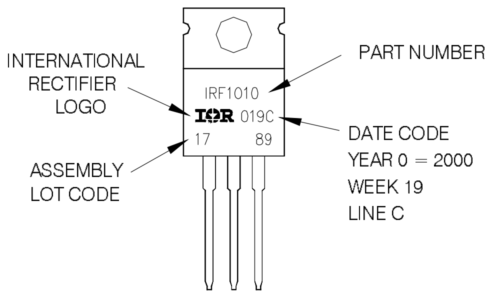
IGBTs, CoPACK
1.– GATE
2.– COLLECTOR
3.– EMITTER

DIODES
1.– ANODE/OPEN
2.– CATHODE
3.– ANODE

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 2000
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead - Free"



TO-220AB packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial market.
Qualification Standards can be found on IR's Web site.

International IOR Rectifier

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